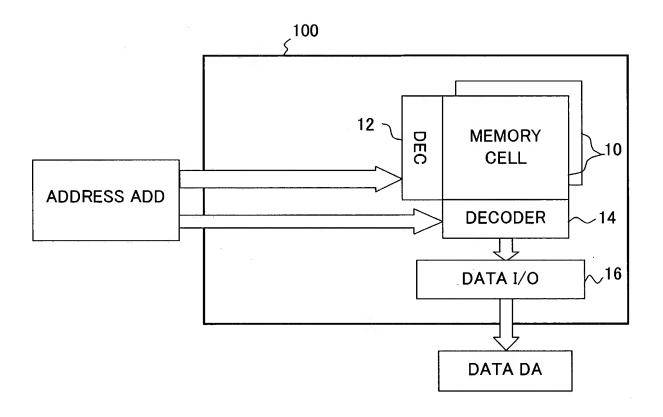
Title: NONVOLATILE SEMICONDUCTOR MEMORY HAVING PARTIAL DATA REWRITING FUNCTION Inventor: Tomohiro NAKAYAMA Application No. New Docket No. 108066-00085

FIG. 1

PRIOR ART

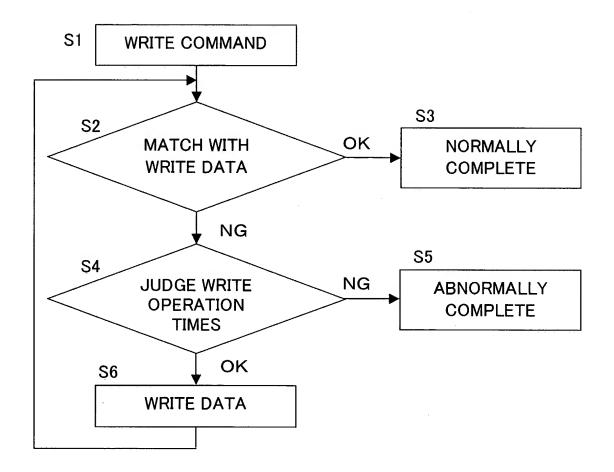


Title: NONVOLATILE SEMICONDUCTOR MEMORY HAVING PARTIAL DATA REWRITING FUNCTION Inventor: Tomohiro NAKAYAMA

Application No. New Docket No. 108066-00085

FIG. 2

PRIOR ART



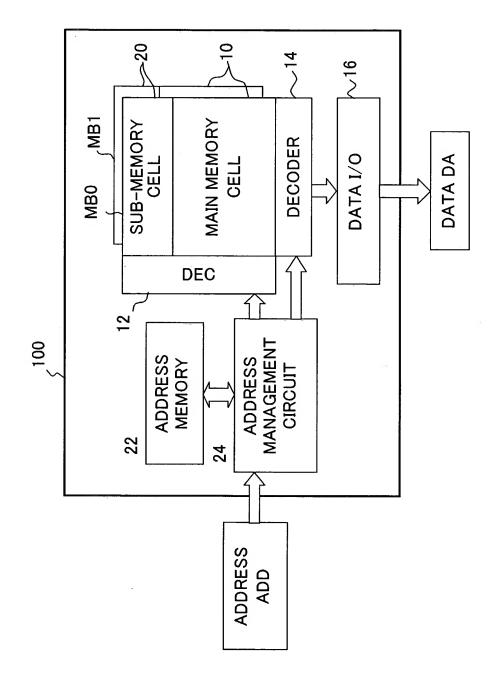
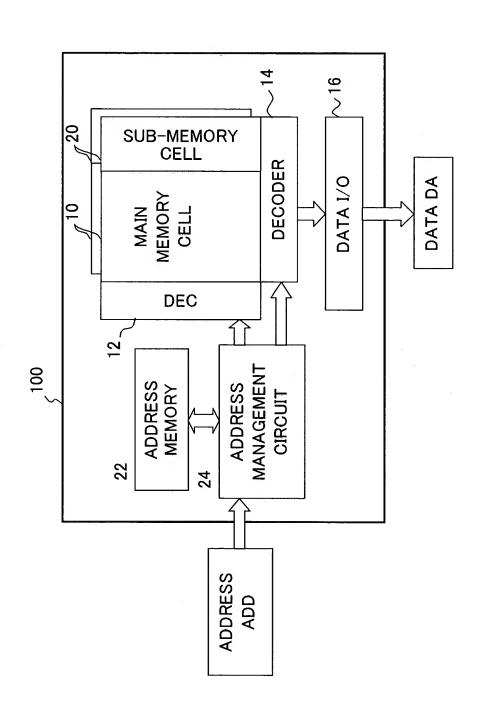
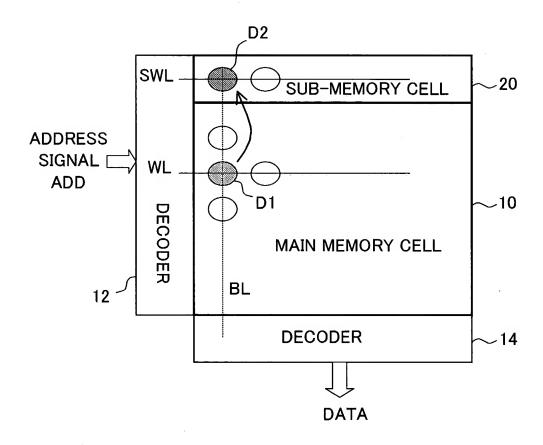


FIG. 4



Title: NONVOLATILE SEMICONDUCTOR-MEMORY HAVING PARTIAL DATA REWRITING FUNCTION Inventor: Tomoliiro NAKAYAMA Application No. New Docket No. 108066-00085 Title: NONVOLATILE SEMICONDUCTOR
MEMORY HAVING PARTIAL DATA
REWRITING FUNCTION
Inventor: Tomohiro NAKAYAMA
Application No. New
Docket No. 108066-00085

FIG. 5



Title: NONVOLATILE SEMICONDUCTOR
MEMORY HAVING PARTIAL DATA
REWRITING FUNCTION
Inventor: Tomohiro NAKAYAMA

Application No. New Docket No. 108066-00085

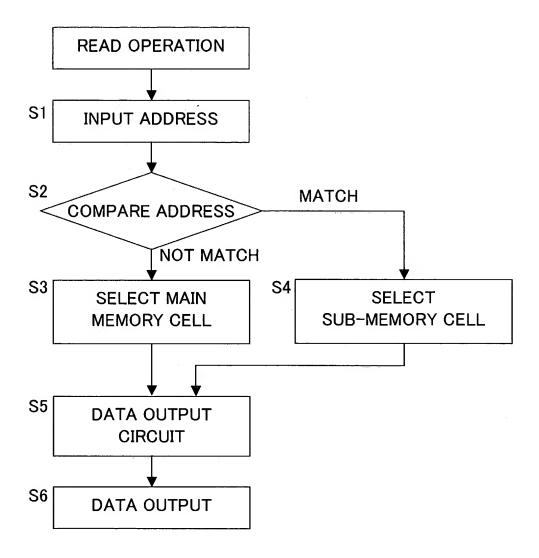
FIG. 6

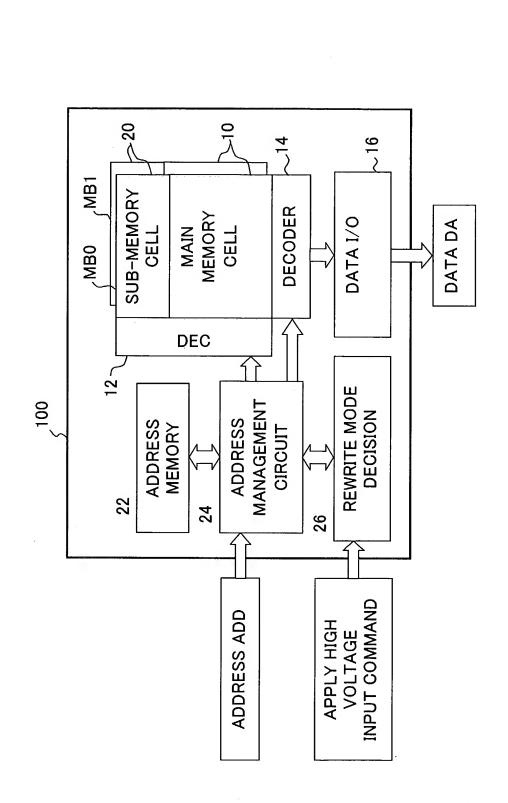
22

MAIN MEMORY ADDRESS ADD	SUB-MEMORY ADDRESS SADD
ADD1 ADD2	000 001 010 011 • •

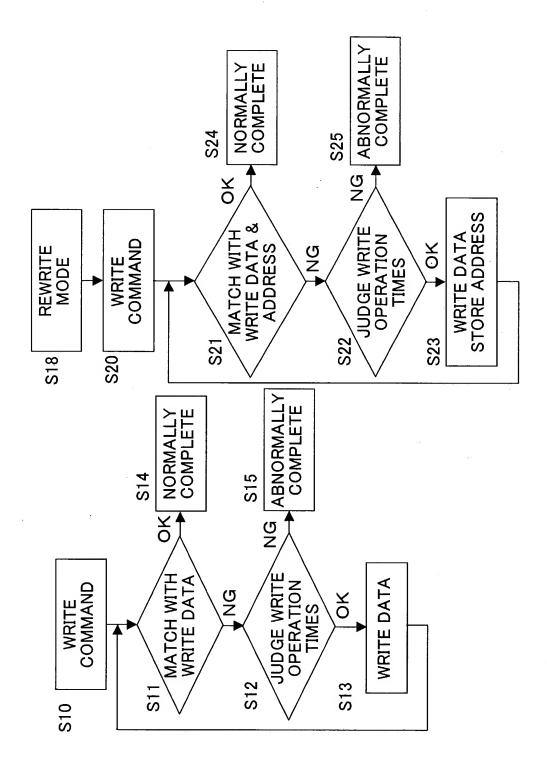
Title: NONVOLATILE SEMICONDUCTOR MEMORY HAVING PARTIAL DATA REWRITING FUNCTION Inventor: Tomohiro NAKAYAMA Application No. New Docket No. 108066-00085

FIG. 7

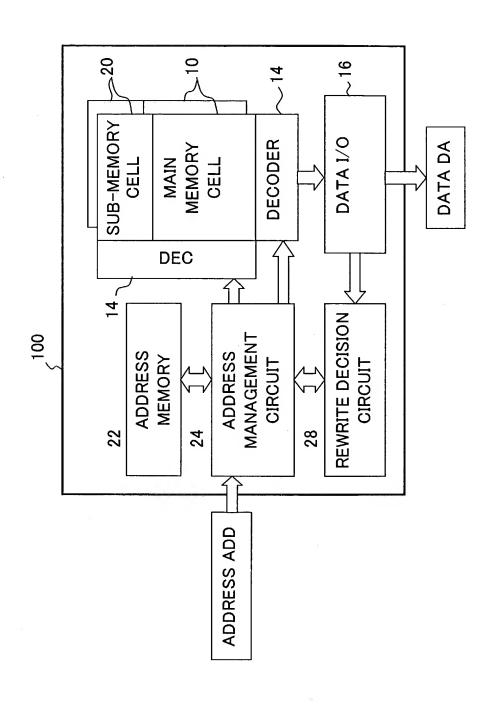


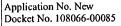


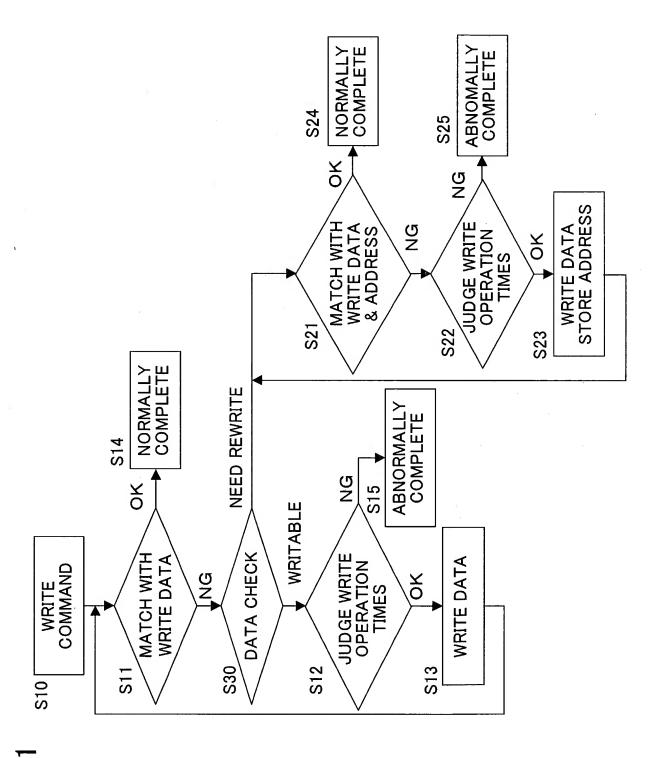
Title: NONVOLATILE SEMICONDUCTOR
MEMORY HAVING PARTIAL DATA
REWRITING FUNCTION
Inventor: Tomohiro NAKAYAMA
Application No. New
Docket No. 108066-00085



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Application No. New Docket No. 108066-00085

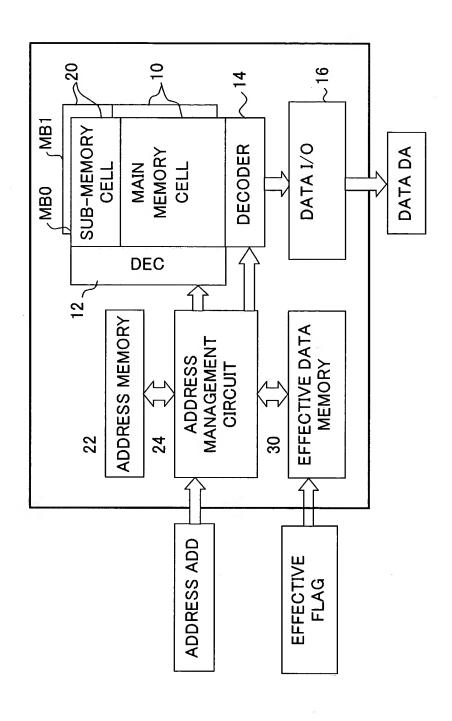


FIG. 1.

Title: NONVOLATILE SEMICONDUCTOR
MEMORY HAVING PARTIAL DATA
REWRITING FUNCTION
Inventor: Tomohiro NAKAYAMA
Application No. New

Docket No. 108066-00085

FIG. 13

